

FIG. 1 – Prior Art

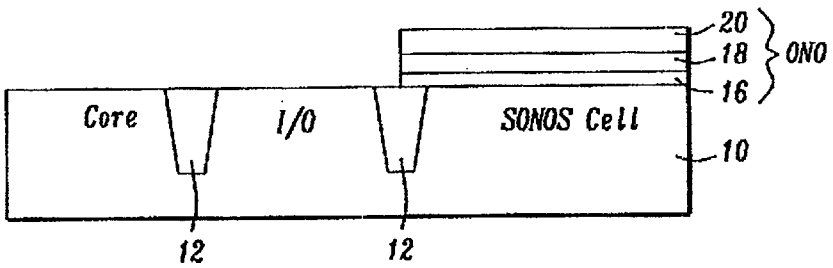


FIG. 2 – Prior Art

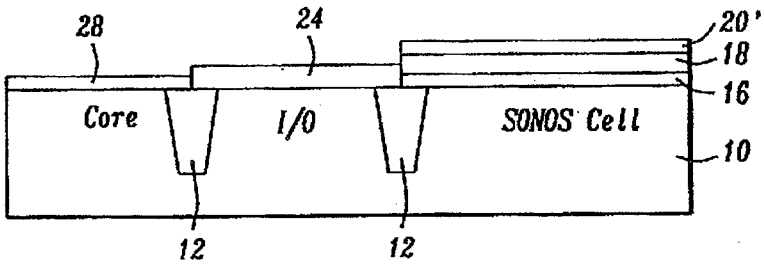


FIG. 3 – Prior Art

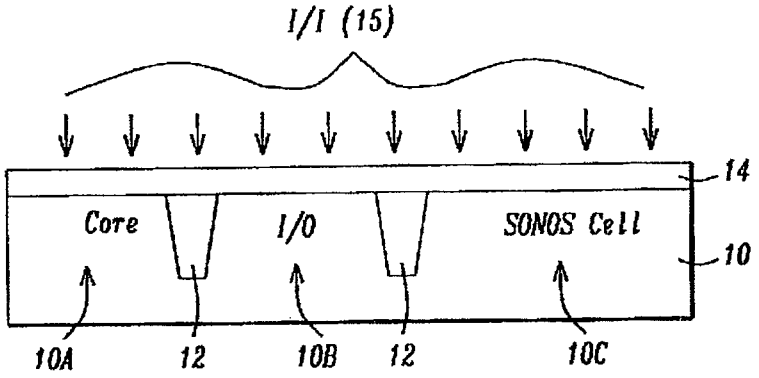


FIG. 4

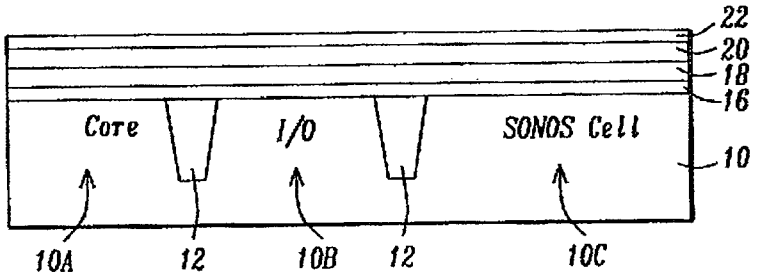


FIG. 5

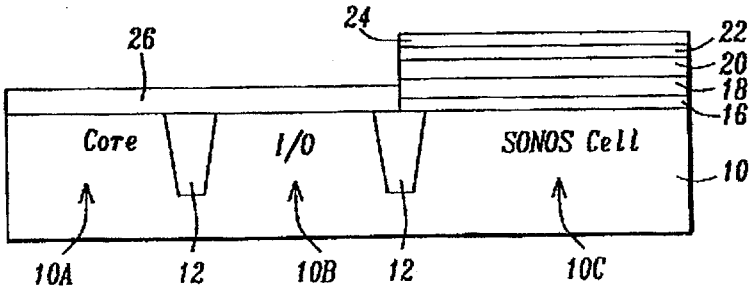


FIG. 6

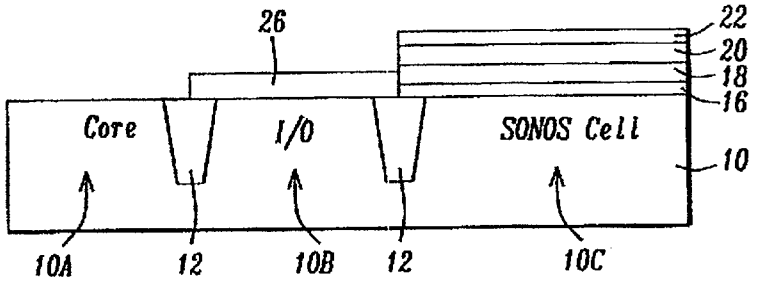


FIG. 7

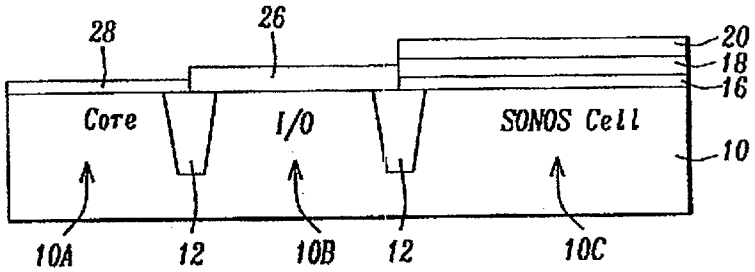


FIG. 8

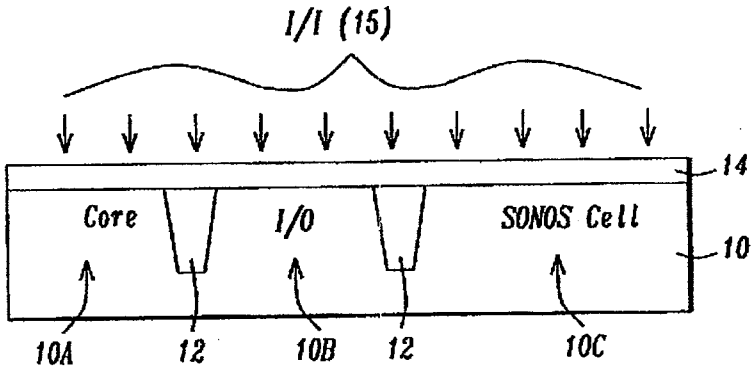


FIG. 9

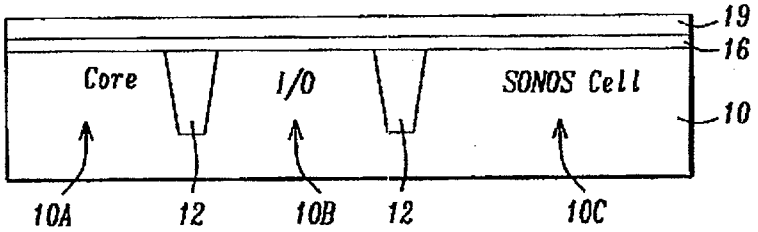


FIG. 10

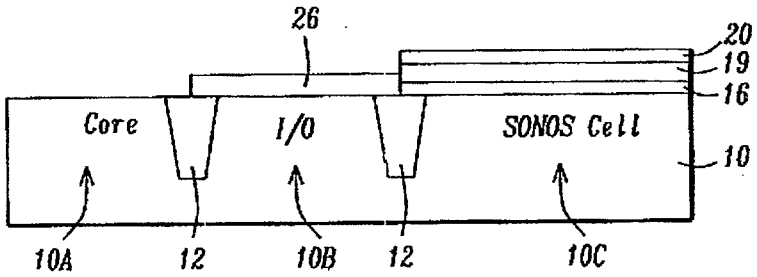


FIG. 11

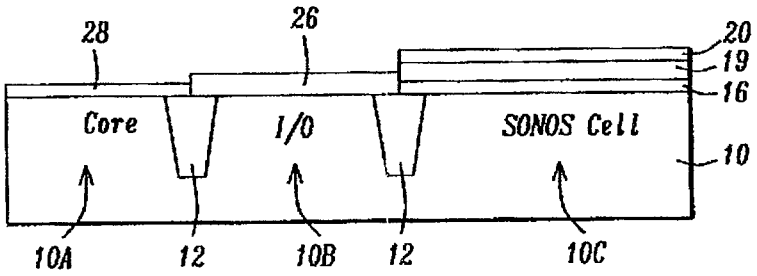


FIG. 12

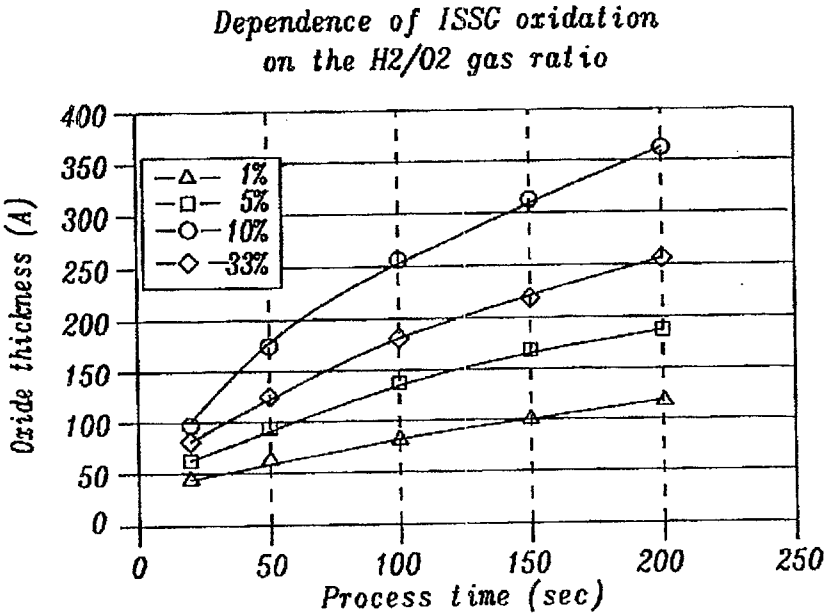

Dependence of ISSC oxidation
on the H2/02 gas ratio
Oxide thickness (A)
Process time (sec)
1%
5%
10%
33%
400
350
300
250
200
150
100
50
0
0
50
100
150
200
250

FIG. 13

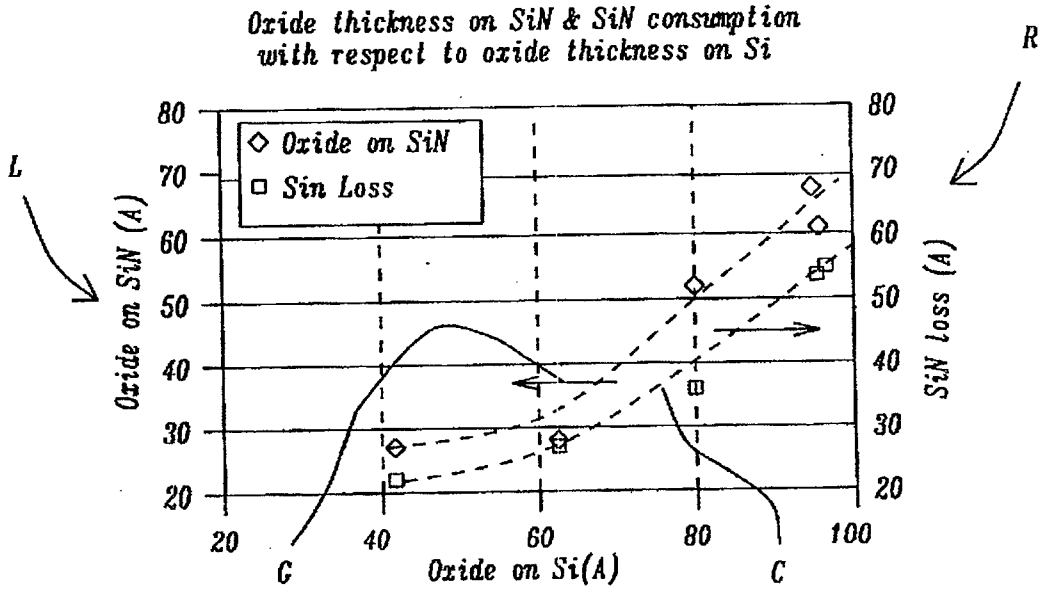

Oxide thickness on SiN & SiN consumption
with respect to oxide thickness on Si
L
R
Oxide on SiN (A)
SiN loss (A)
Oxide on SiN
Sin Loss
Oxide on Si(A)
C
C
80
70
60
50
40
30
20
20
40
60
80
100

FIG. 14